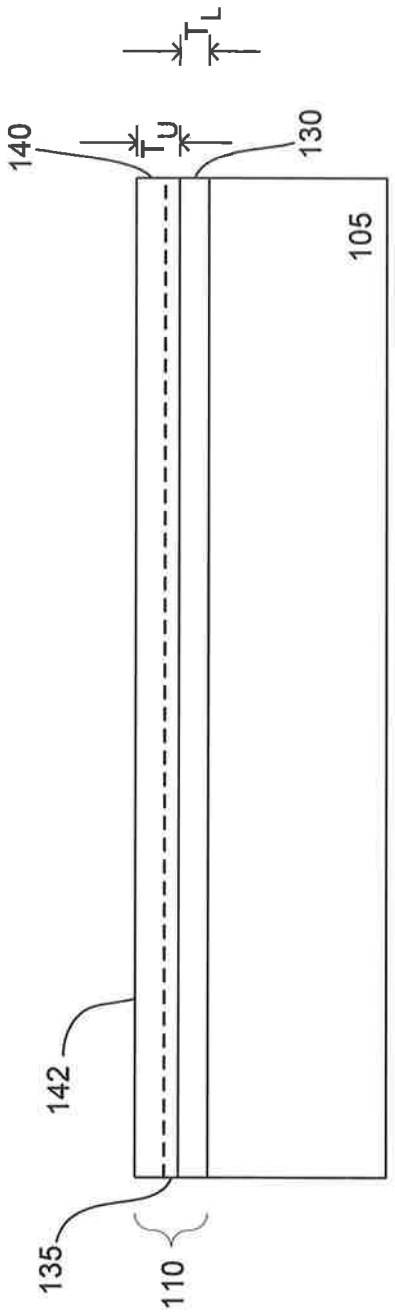


Fig. 1a

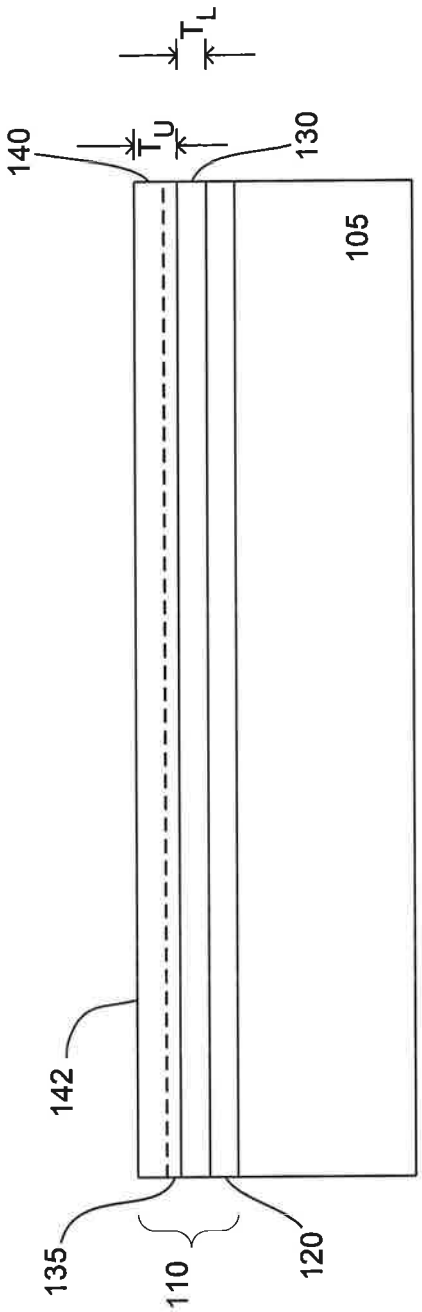


Fig. 1b

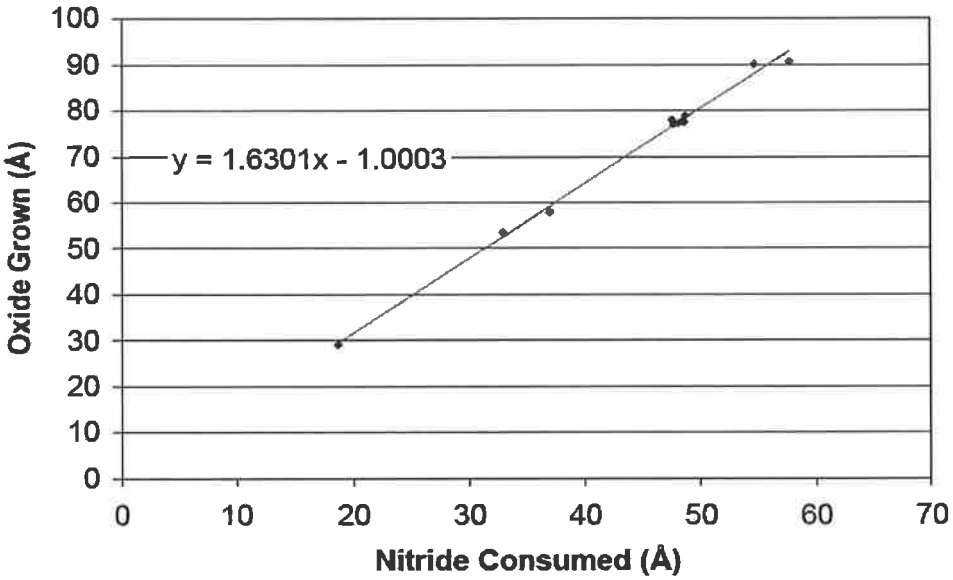

100
90
80
70
60
50
40
30
20
10
0
Oxide Grown (Å)
y = 1.6301x - 1.0003
0
10
20
30
40
50
60
70
Nitride Consumed (Å)

Fig. 2

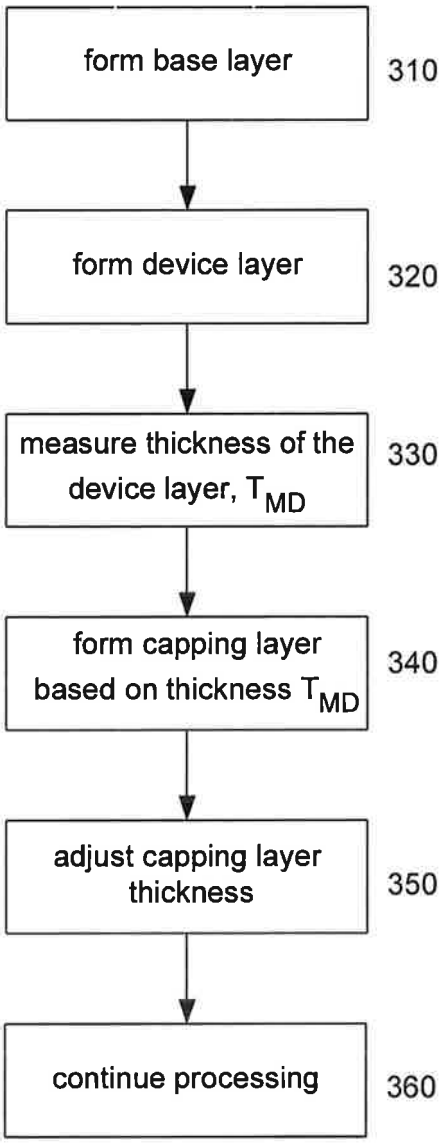

form base layer
310
form device layer
320
measure thickness of the device layer, T_{MD}
330
form capping layer based on thickness T_{MD}
340
adjust capping layer thickness
350
continue processing
360
300

Fig. 3

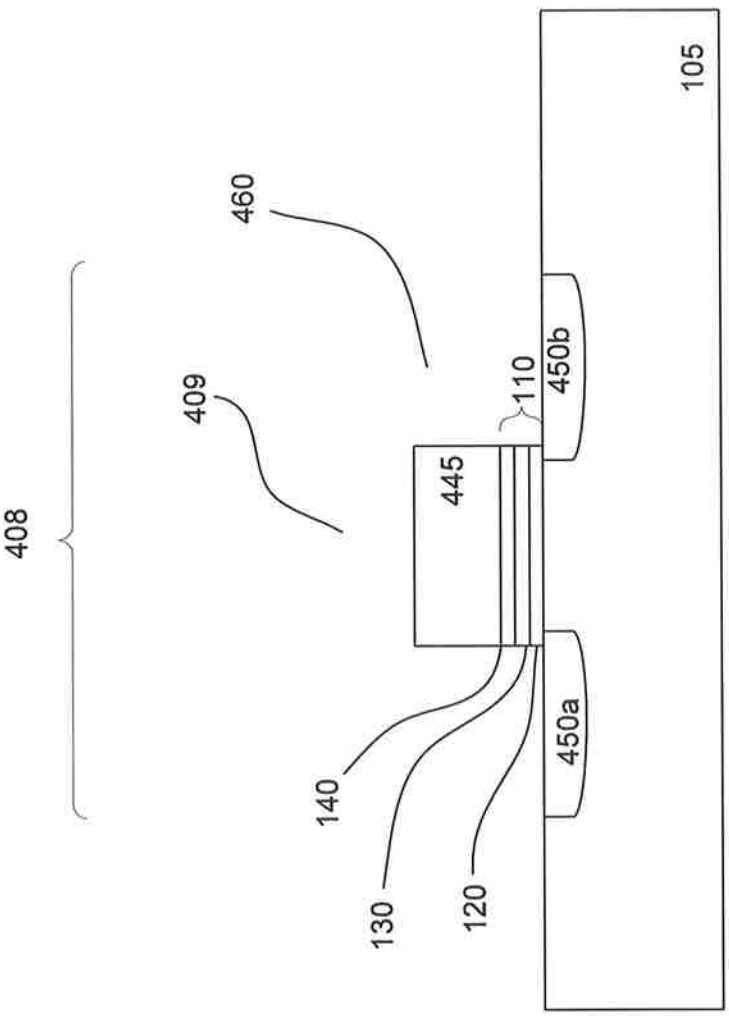


Fig. 4

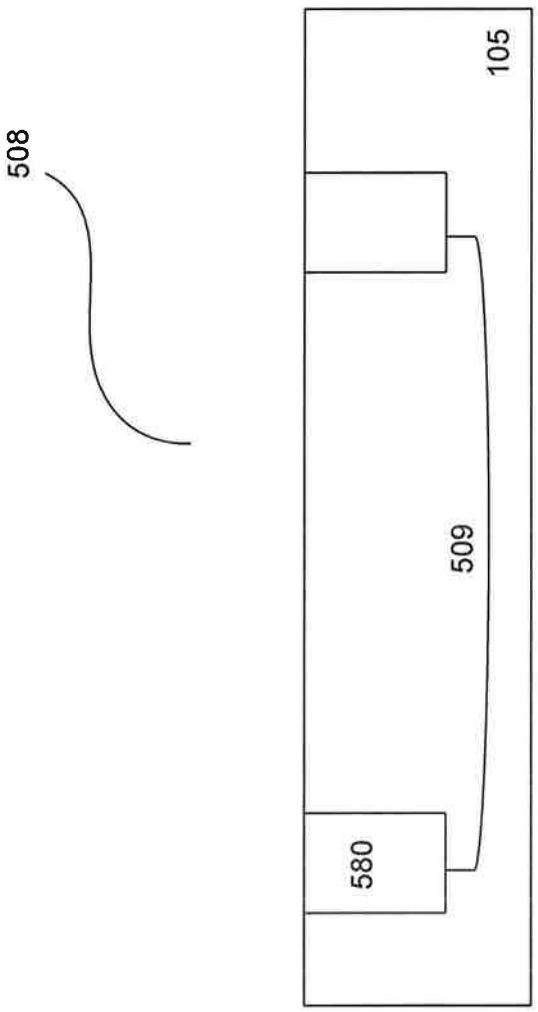


Fig. 5a

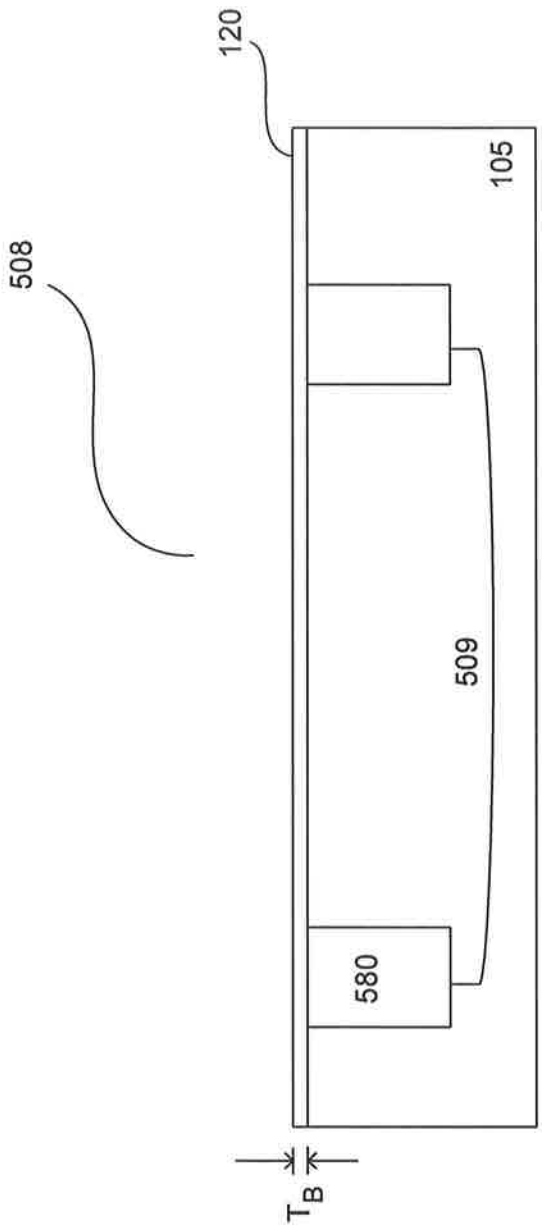


Fig. 5b

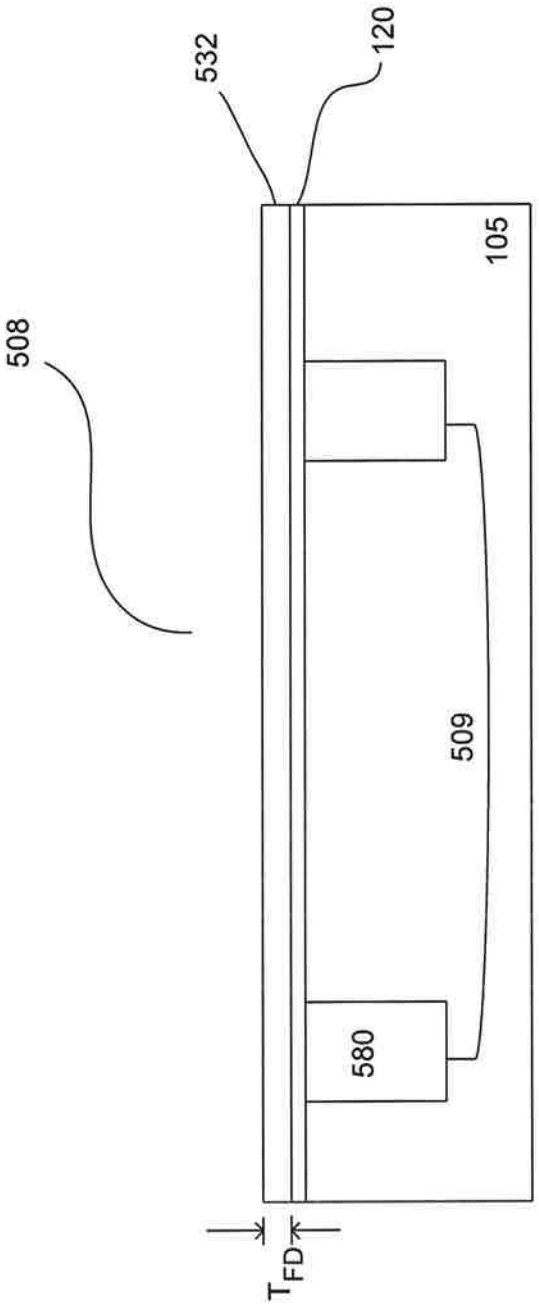


Fig. 5c

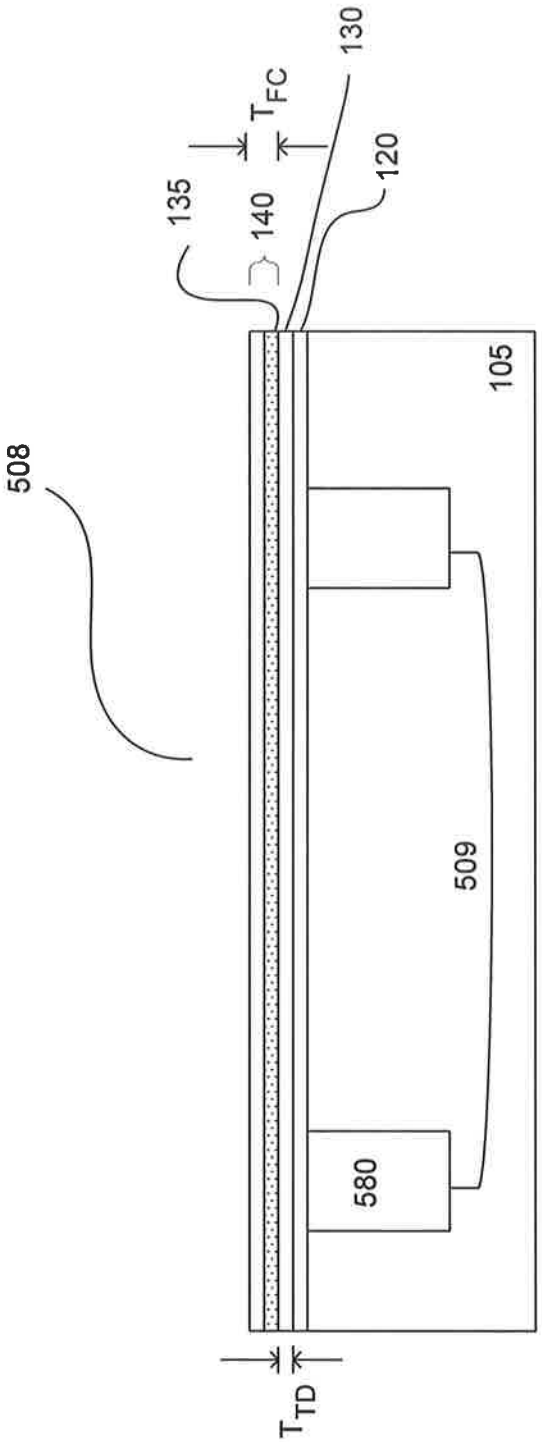


Fig. 5d

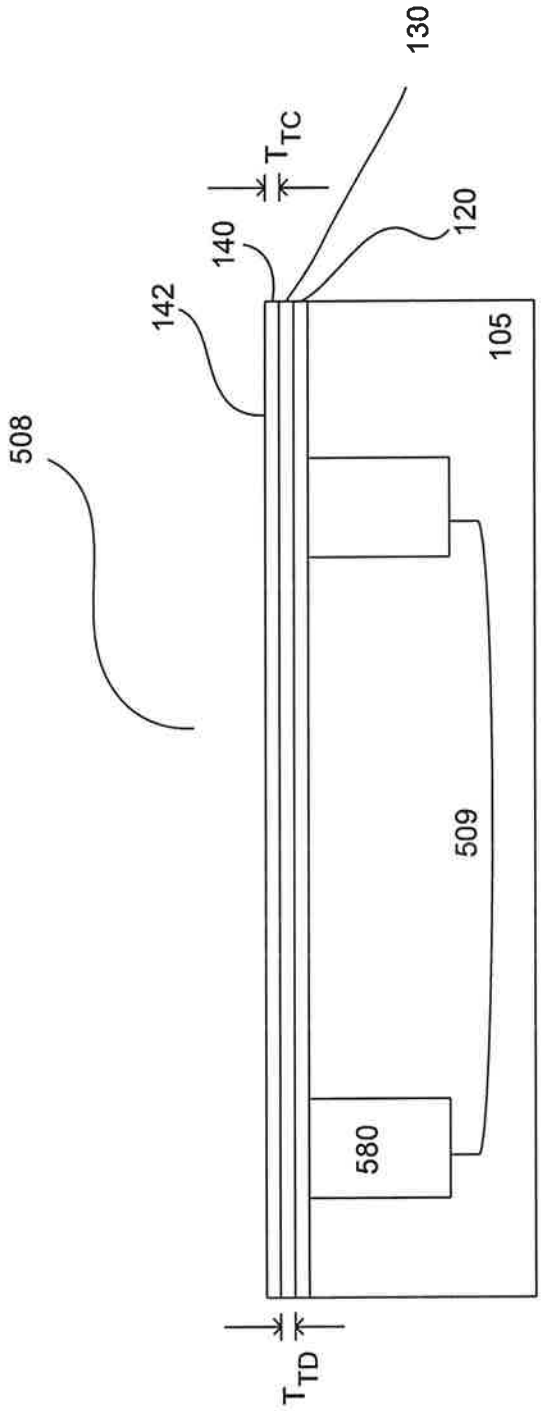


Fig. 5e

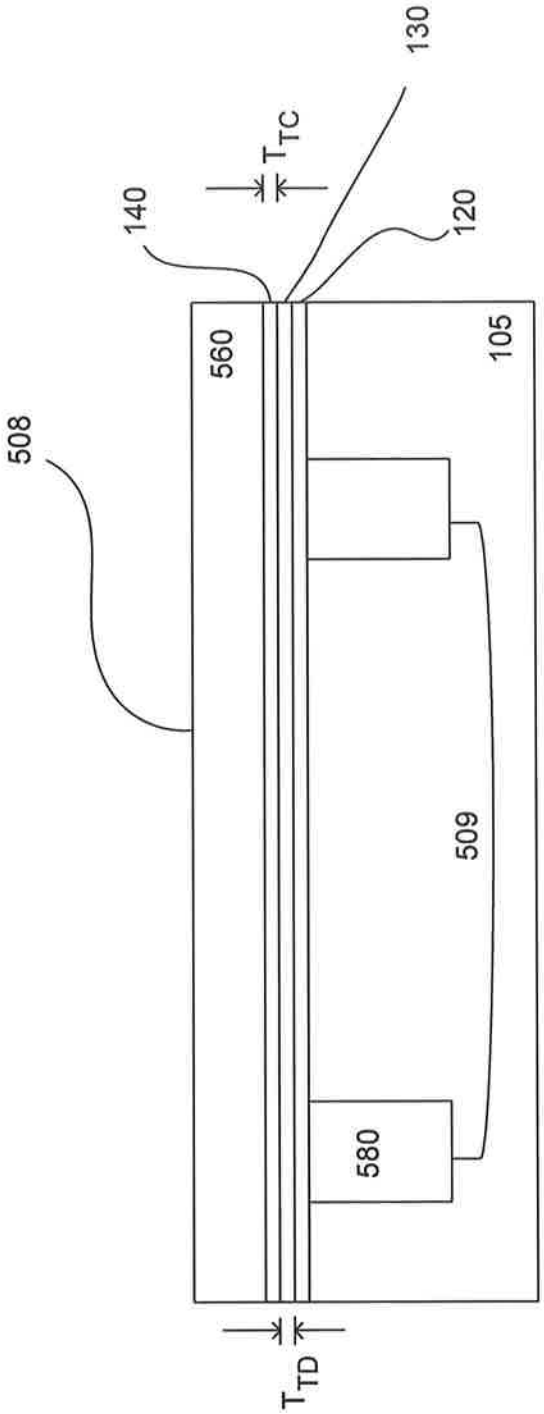


Fig. 5f

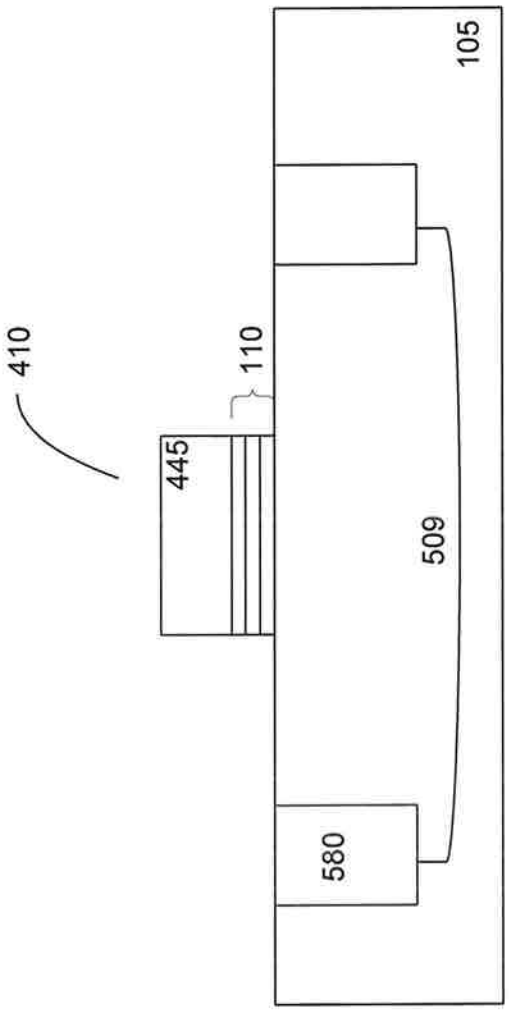


Fig. 5g